



AC817-40Q

45V NPN SMALL SIGNAL TRANSISTOR IN SOT23

Description

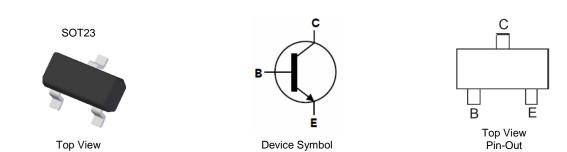
This Bipolar Junction Transistor (BJT) is designed to meet the stringent requirements of Automotive Applications.

Features

- BV_{CEO} > 45V
- I_C = 0.5A Continuous Collector Current
- I_{CM} = 1A Peak Pulse Current
- Complementary PNP Types: BC807-16
- Ideally Suited for Automatic Insertion
- Epitaxial Planar Die Construction
- For Switching and AF Amplifier Applications
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound; UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.008 grams (Approximate)



Ordering Information (Note 5)

Part number	Compliance	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
AC817-40Q-7	Automotive	2D8	7	8	3,000

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

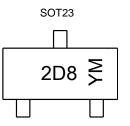
2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to http://www.diodes.com/product_compliance_definitions.html.

5. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



2D8 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: E = 2017) M = Month (ex: 9 = September)

Date Code Key

Year	2017	2018	2019	2020	2021	2022	2023	2024	2025	2026	2027	2028
Code	E	F	G	Н	I	J	К	L	М	Ν	0	Р
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec



Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	50	V
Collector-Emitter Voltage	V _{CEO}	45	V
Emitter-Base Voltage	V _{EBO}	5.0	V
Collector Current	lc	0.5	А
Peak Collector Current	Ісм	1.0	A
Peak Base Current	I _{BM}	200	mA

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Power Dissipation	(Note 6)	D	310	mW
	(Note 7)	PD	350	ITIVV
Thermal Desistance Junction to Ambient	(Note 6)	D	403	°C/W
Thermal Resistance, Junction to Ambient	(Note 7)	R _{θJA}	357	C/VV
Thermal Resistance, Junction to Leads	(Note 8)	R _{θJL}	350	°C/W
Operating and Storage Temperature Range		T _{J,} T _{STG}	-65 to +150	°C

ESD Ratings (Note 9)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	8,000	V	3B
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

6. For a device mounted on minimum recommended pad layout FR-4 PCB with high coverage of single sided 1oz copper; device is measured under still air Notes: For a device mounted on minimum recommended pad layout FR-4 PCB with high conditions whilst operating in a steady-state.
 Same as Note 6, except mounted on 15mm x 15mm 1oz copper.
 Thermal resistance from junction to solder-point (at the end of the collector lead).
 Refer to JEDEC specification JESD22-A114 and JESD22-A115.

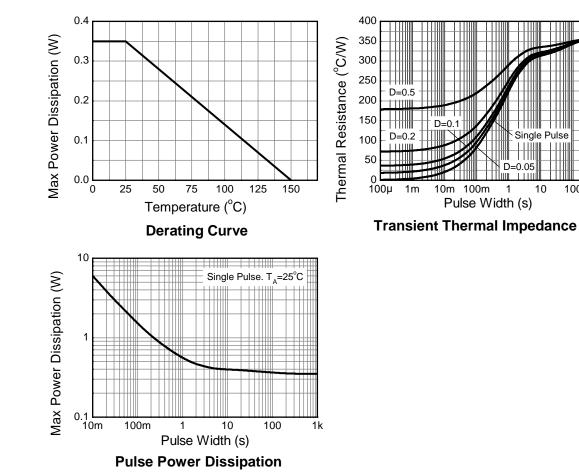


10

100

1k

Thermal Characteristics and Derating Information



AC817-40Q Document number: DS40019 Rev. 1 - 2



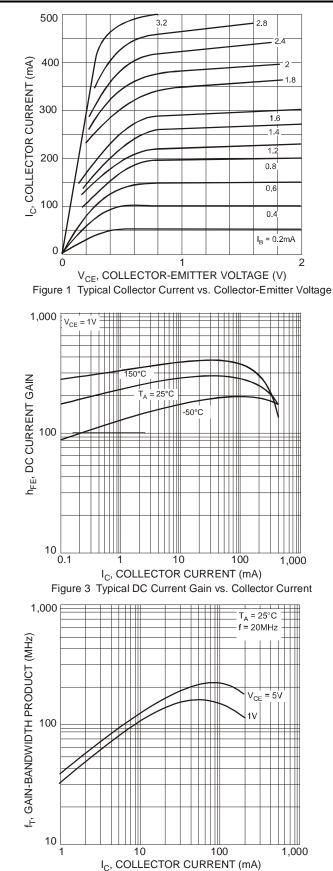
Electrical Characteristics ($@T_A = +25^{\circ}C$, unless otherwise specified.)

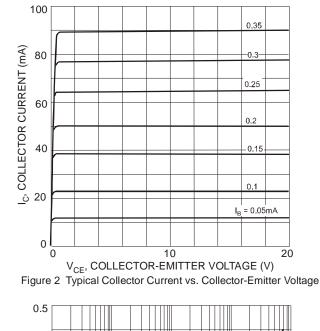
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	50	_	-	V	I _C = 100μA
Collector-Emitter Breakdown Voltage	BV _{CEO}	45	—	—	V	$I_{\rm C} = 10 {\rm mA}$
Emitter-Base Breakdown Voltage	BV _{EBO}	5	_	-	V	I _C = 100μA
Collector-Emitter Cut-Off Current	10-0			100	nA	$V_{CE} = 45V$
	ICES			5.0	μA	$V_{CE} = 25V, T_J = +150^{\circ}C$
Emitter-Base Cut-Off Current	I _{EBO}			100	nA	$V_{EB} = 5.0V$
DC Current Gain (Note 10)	h	250		600		$V_{CE} = 1.0V, I_{C} = 100mA$
	h _{FE}	170		—		$V_{CE} = 1.0V, I_{C} = 300mA$
Collector-Emitter Saturation Voltage (Note 10)	V _{CE(SAT)}	_	_	0.7	V	$I_{\rm C} = 500$ mA, $I_{\rm B} = 50$ mA
Base-Emitter Voltage (Note 10)	V _{BE}	_	_	1.2	V	$V_{CE} = 1.0V, I_{C} = 300mA$
Gain Bandwidth Product	f⊤	100	—	—	MHz	$V_{CE} = 5.0V, I_C = 10mA,$ f = 50MHz
Collector-Base Capacitance	Ссво	_	—	12	pF	V _{CB} = 10V, f = 1.0MHz

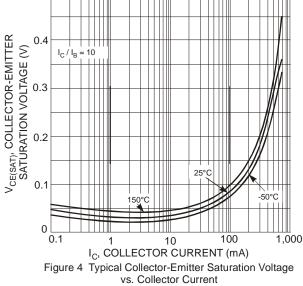
Note: 10. Measured under pulsed conditions. Pulse width \leq 300µs. Duty cycle \leq 2%.



Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)







AC817-40Q Document number: DS40019 Rev. 1 - 2

Figure 5 Gain-Bandwidth Product vs. Collector Current

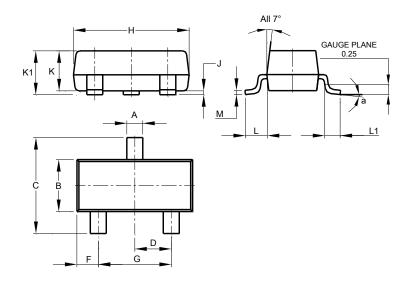


AC817-40Q

Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23

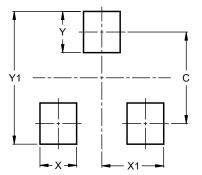


SOT23						
Dim	Min	Max	Тур			
Α	0.37	0.51	0.40			
В	1.20	1.40	1.30			
С	2.30	2.50	2.40			
D	0.89	1.03	0.915			
F	0.45	0.60	0.535			
G	1.78	2.05	1.83			
Η	2.80	3.00	2.90			
J	0.013	0.10	0.05			
Κ	0.890	1.00	0.975			
K1	0.903	1.10	1.025			
L	0.45	0.61	0.55			
L1	0.25	0.55	0.40			
Μ	0.085	0.150	0.110			
а	0°	8°				
All	Dimens	ions in	mm			

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23



Dimensions	Value (in mm)
С	2.0
Х	0.8
X1	1.35
Y	0.9
Y1	2.9



IMPORTANT NOTICE

DIODES INCORPORATED MAKES NO WARRANTY OF ANY KIND, EXPRESS OR IMPLIED, WITH REGARDS TO THIS DOCUMENT, INCLUDING, BUT NOT LIMITED TO, THE IMPLIED WARRANTIES OF MERCHANTABILITY AND FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION).

Diodes Incorporated and its subsidiaries reserve the right to make modifications, enhancements, improvements, corrections or other changes without further notice to this document and any product described herein. Diodes Incorporated does not assume any liability arising out of the application or use of this document or any product described herein; neither does Diodes Incorporated convey any license under its patent or trademark rights, nor the rights of others. Any Customer or user of this document or products described herein in such applications shall assume all risks of such use and will agree to hold Diodes Incorporated and all the companies whose products are represented on Diodes Incorporated website, harmless against all damages.

Diodes Incorporated does not warrant or accept any liability whatsoever in respect of any products purchased through unauthorized sales channel. Should Customers purchase or use Diodes Incorporated products for any unintended or unauthorized application, Customers shall indemnify and hold Diodes Incorporated and its representatives harmless against all claims, damages, expenses, and attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized application.

Products described herein may be covered by one or more United States, international or foreign patents pending. Product names and markings noted herein may also be covered by one or more United States, international or foreign trademarks.

This document is written in English but may be translated into multiple languages for reference. Only the English version of this document is the final and determinative format released by Diodes Incorporated.

LIFE SUPPORT

Diodes Incorporated products are specifically not authorized for use as critical components in life support devices or systems without the express written approval of the Chief Executive Officer of Diodes Incorporated. As used herein:

- A. Life support devices or systems are devices or systems which:
 - 1. are intended to implant into the body, or
 - 2. support or sustain life and whose failure to perform when properly used in accordance with instructions for use provided in the labeling can be reasonably expected to result in significant injury to the user.
- B. A critical component is any component in a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or to affect its safety or effectiveness.

Customers represent that they have all necessary expertise in the safety and regulatory ramifications of their life support devices or systems, and acknowledge and agree that they are solely responsible for all legal, regulatory and safety-related requirements concerning their products and any use of Diodes Incorporated products in such safety-critical, life support devices or systems, notwithstanding any devices- or systems-related information or support that may be provided by Diodes Incorporated. Further, Customers must fully indemnify Diodes Incorporated and its representatives against any damages arising out of the use of Diodes Incorporated products in such safety-critical, life support devices or systems.

Copyright © 2017, Diodes Incorporated

www.diodes.com

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for Bipolar Transistors - BJT category:

Click to view products by Diodes Incorporated manufacturer:

Other Similar products are found below :

 BC559C
 MCH4017-TL-H
 MMBT-2369-TR
 BC546/116
 NJVMJD148T4G
 NTE16
 NTE195A
 IMX9T110
 2N4401-A
 2N6728
 2SA1419T

 TD-H
 2SB1204S-TL-E
 2SC5488A-TL-H
 FMC5AT148
 2N2369ADCSM
 2N2907A
 2N3904-NS
 2N5769
 2SC4618TLN
 CPH6501-TL-E

 BC856BW-13-F
 US6T6TR
 BAX18/A52R
 BC556/112
 IMZ2AT108
 MMST8098T146
 MCH6102-TL-E
 BC846B-13-F
 2N3879
 30A02MH

 TL-E
 NTE13
 NTE282
 NTE323
 NTE81
 JANTX2N2920L
 JANSR2N2907AUB
 CMLT3946EG TR
 SNSS40600CF8T1G

 CMLT3906EG TR
 GRP-DATA-JANS2N2907AUB
 GRP-DATA-JANS2N2907AUB
 GRP-DATA-JANS2N3019
 MSB30KH

 13
 2N2221AUB
 2SD1815T-TL-E
 2N6678
 2N2907Ae4